

RJK0353DPA-01#J0B

RJK0353DPA-01#J0B Information



For Reference Only

Part Number RJK0353DPA-01#J0B

ManufacturerRenesas Electronics AmericaCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 35A 2WPACK

Package 8-PowerWDFN

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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RJK0353DPA-01#J0B Specifications

Manufacturer Part Number Manufacturer Renesas Electronics America Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 8-PowerWDFN Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **Emissions America Renesas Electronics America Renesas Electronics America 1
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-PowerWDFN Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 8-PowerWDFN N-Channel 30V 4.5V, 10V 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 14nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds
Transistors - FETs, MOSFETs - Single Package 8-PowerWDFN Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 35A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 14nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 2180pF @ 10V
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Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 35A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds MOSFET (Metal Oxide) 30V 4.5V, 10V 2.5V @ 1mA 2.5V @ 1mA 14nC @ 4.5V 2180pF @ 10V
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 35A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 35A (Ta) 4.5V, 10V 2.5V @ 1mA 2.5V @ 1mA 2.5V @ 1mA 2.5V @ 1mA
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Gate Charge (Qg) (Max) @ Vgs 14nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 2180pF @ 10V
Input Capacitance (Ciss) (Max) @ Vds 2180pF @ 10V
$Vgs (Max)$ $\pm 20V$
FET Feature -
Power Dissipation (Max) 40W (Tc)
Rds On (Max) @ Id, Vgs 5.2 mOhm @ 17.5A, 10V
Operating Temperature 150°C (TJ)
Mounting Type Surface Mount
Supplier Device Package 8-WPAK
Package / Case 8-PowerWDFN
Report err

RJK0353DPA-01#J0B Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

RJK0353DPA-01#J0B Payment Methods



















RJK0353DPA-01#J0B Shipping Methods













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